

# FORMATION OF COPPER SULFIDE LAYERS ON POLYPROPYLENE BY CBD METHOD

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## INTRODUCTION

Nanocrystalline copper sulfide ( $\text{Cu}_x\text{S}$ ), deposited as a thin film on the different substrates, is considered to be a promising material for solar energy conversion systems, because of its structural and electrical properties. One of the interesting semiconducting layers is copper sulfide because of its metal-like electrical conductivity, chemical-sensing capability, and ideal characteristics for solar energy absorption. Consequently, polymers modified with copper sulfide layers are used as conductive substrates for deposition of metals and semiconductors; as gas sensors functioning at temperatures tending to room temperature; in thermoelectric applications; in solar cells; in lithium ion batteries [1].

The aim of the work was to characterize the surface of the PP/ $\text{Cu}_x\text{S}$  composite by scanning electron microscopy (SEM/EDX) and to measure the sheet resistance.

## EXPERIMENTAL

This work reports the preparation of  $\text{Cu}_x\text{S}$  electroconductive layers on polypropylene films (150  $\mu\text{m}$  thicknesses (KWH Plast, Finland) using the CBD method at room temperature [2,3].

The etching solution  $\text{H}_2\text{SO}_4/\text{H}_3\text{PO}_4$  (1:1) saturated with  $\text{CrO}_3$  (90  $^\circ\text{C}$ , 25 min) was used for the oxidation of the surface of PP.

The deposition of the  $\text{Cu}_x\text{S}$  thin films was carried out at room temperature using a mixture of 0.05 M  $\text{CuCl}_2$  and 0.05 M  $\text{Na}_2\text{S}_2\text{O}_3$  solutions (pH 3) for 16 h. The deposition process was carried out by repeating such deposition cycles 3 times.

The films were annealed at 80  $^\circ\text{C}$  for 30 minutes in air atmosphere.

Samples of the PP/ $\text{Cu}_x\text{S}$  composite were investigated by SEM/EDX, and electrical sheet resistivity was measured using special electrodes.

## RESULTS

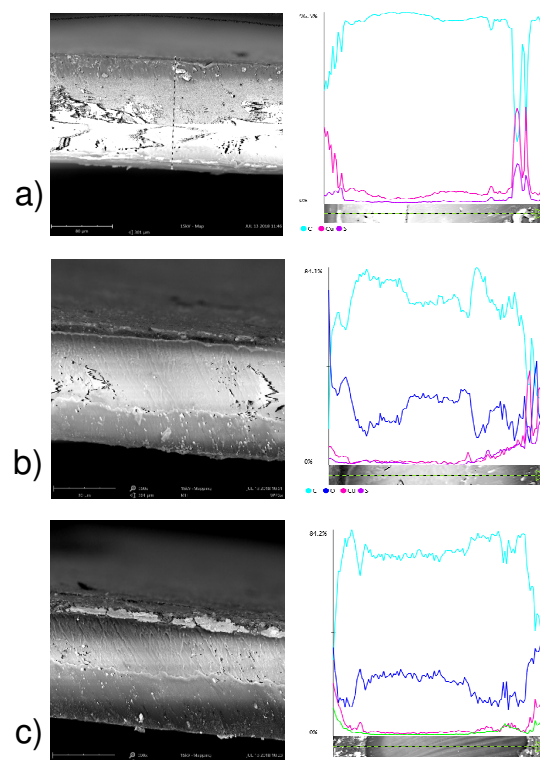
The room temperature electrical resistivity of the formed layer after 1st deposition cycle was about 10  $\text{k}\Omega/\square$ , after 2nd – 180  $\Omega/\square$ , and after 3rd – 130  $\Omega/\square$ . After annealing electrical resistivity decreased to 7  $\text{k}\Omega/\square$ , 170  $\Omega/\square$  and 110  $\Omega/\square$  accordingly.

Analysis of SEM images of PP/ $\text{Cu}_x\text{S}$  films showed that after 3 deposition cycles, the PP substrate was completely covered by  $\text{Cu}_x\text{S}$  particles. Cross sectional image given in Fig. demonstrated growing of  $\text{Cu}_x\text{S}$  layer with increasing of the cycle number.

EDX analysis showed that  $\text{Cu}_x\text{S}$  is formed on the surface of the PP film, and a negligible amount of copper and sulfur diffused into the PP matrix (Table and Fig.)

**Table.** Concentration of elements in PP/ $\text{Cu}_x\text{S}$  composite after I, II and III deposition cycles

Depth, $\mu\text{m}$	Element Symbol	Atomic Concentration			Weight Concentration			Stoichiometric Concentration		
		I	II	III	I	II	III	I	II	III
0	C	42.05	68.46	71.96	24.76	55.97	58.53	75.30	94.80	94.56
	Cu	12.27	2.60	3.08	38.22	11.27	13.26	21.97	3.61	4.05
	S	1.52	1.15	1.06	2.39	2.51	2.31	2.72	1.59	1.40
5	C	60.33	79.77	79.50	52.24	74.01	70.44	98.70	99.49	97.69
	Cu	0.48	0.20	1.35	2.18	0.98	6.35	0.78	0.25	1.66
	S	0.32	0.20	0.53	0.73	0.51	1.25	0.52	0.26	0.65
15	Cu	0.00	1.14	1.14	0.00	0.67	0.67	0.00	0.19	0.19
	S	0.00	0.02	0.02	0.00	0.04	0.04	0.00	0.02	0.02



**Fig.** Cross section SEM images and distribution of elements of PP/ $\text{Cu}_x\text{S}$  composite formed by I (a), II (b) and III (c) cycles

## CONCLUSIONS

Formed by CBD  $\text{Cu}_x\text{S}$  layers are thin, and uniform, and a small amount of Cu and S was diffused into the PP matrix. The electrical resistivity of composites PP/ $\text{Cu}_x\text{S}$  decreased with an increasing number of deposition cycles, and, after annealing, the decrease in electrical resistivity is insignificant.

## REFERENCES

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